

41. (New) The method according to Claim 22 in which the layer of microcavities is formed in a semiconductor substrate.

42. (New) The method according to Claim 41, in which the substrate is in silicon and the embedded layer is a layer of silicon oxide.--

REMARKS

Claims 22-42 are active in the present application. Support for these claims is found in Claims 1-21 and the specification as filed herewith. No new matter is believed to have been added by these amendments. An action on the merits and allowance of the claims is solicited.

Respectfully submitted,

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